

Serial No. 10/532,651
Response to Office Action of December 20, 2006
Amendment dated January 19, 2007

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AMENDMENTS TO THE CLAIMS:

This listing of claims shall replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A liquid ejecting device comprising:

at least one heating element and at least one metal oxide field effect transistor to drive said heating element which is formed such that said heating element is distally located from, and driven by, said metal oxide field effect transistor, so as to heat a liquid contained in a liquid chamber, thereby ejecting said liquid, characterized in that said metal oxide field effect transistor has a polycide gate or a metal gate.

2. (Currently Amended) The liquid ~~delivery head~~ ejecting device as defined in Claim 1, wherein the gate electrode has a gate length ~~no larger~~ shorter than 2 μm .

3. (Previously Presented) A liquid ejecting device for ejecting liquid droplets toward an object comprising:

a liquid delivery head having at least one heating element and at least one metal oxide field effect transistor distally located from said heating element wherein said metal oxide field effect transistor drives said heating element which is formed on a substrate such that said heating element heats a liquid contained in a liquid chamber, thereby ejecting said liquid wherein said metal oxide field effect transistor has a polycide gate or a metal gate.

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4. (Previously Presented) A process for production of a liquid ejecting device

comprising:

forming a metal oxide field effect transistor;

forming at least one wiring element electrically connected to the metal oxide field effect transistor;

forming a heating element, distally located from said metal oxide field effect transistor, connected to said wiring element such that the heating element is electrically connected to said metal oxide field effect transistor; and

forming a liquid chamber coupled to said heating element; wherein said metal oxide field effect transistor has a polycide gate or a metal gate.